



STN210D



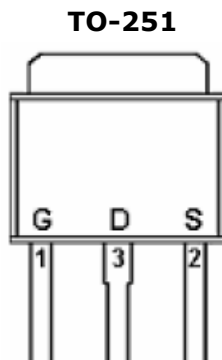
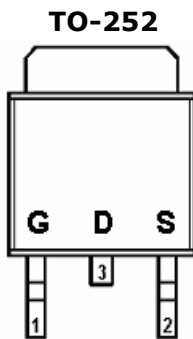
N Channel Enhancement Mode MOSFET

80.0A

DESCRIPTION

STN210D uses Trench MOSFET technology that is uniquely optimized to provide the most efficient high frequency switching performance. It has been optimized for low gate charge, low $R_{DS(ON)}$ and fast switching speed.

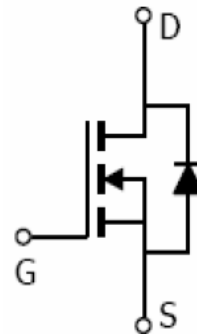
PIN CONFIGURATION (D-PAK)



FEATURE

- 30V/20A, $R_{DS(ON)} = 3m\Omega$
@ $V_{GS} = 10V$
- 30V/20A, $R_{DS(ON)} = 4m\Omega$
@ $V_{GS} = 4.5V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- TO-252, TO-251 package design

PART MARKING



Y : Year Code
A : Date Code
B : Process Code

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STN210D



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ABSOLUTE MAXIMUM RATINGS (Ta = 25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	VDSS	30	V
Gate-Source Voltage	VGSS	±20	V
Continuous Drain Current (TJ=150°C)	ID	80 55	A
TA=25°C TA=100°C			
Pulsed Drain Current	IDM	360	A
Continuous Source Current (Diode Conduction)	IS	23	A
Power Dissipation	PD	150	W
TA=25°C			
Operation Junction Temperature	TJ	175	°C
Storage Temperature Range	TSTG	-55/175	°C
Thermal Resistance-Junction to Ambient	RθJA	110	°C/W



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ELECTRICAL CHARACTERISTICS (Ta = 25°C Unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.3		2.5	V
Gate Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$			1	uA
		$V_{DS}=30V, V_{GS}=0V$ $T_J=55^\circ C$			5	
Drain-source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$ $V_{GS}=4.5V, I_D=20A$		2.4 3.7	3 4.7	mΩ
Forward Transconductance	g_{fs}	$V_{DS}=5V, I_D=20A$	80			S
Diode Forward Voltage	V_{SD}	$I_S=1.0A, V_{GS}=0V$			1.0	V
Dynamic						
Total Gate Charge	Q_g	$V_{DS}=15V, V_{GS}=10V$ $I_D=20A$			120	nC
Gate-Source Charge	Q_{gs}				30	
Gate-Drain Charge	Q_{gd}				40	
Input Capacitance	C_{iss}	$V_{DS}=15V, V_{GS}=0V$ $F=1MHz$		7780		pF
Output Capacitance	C_{oss}			1805		
Reverse Transfer Capacitance	C_{rss}			435		
Turn-On Time	$t_{d(on)}$ t_r	$V_{DS}=15V, R_L=0.75\Omega$ $V_{GS}=10V, R_{GEN}=3\Omega$		12		nS
				11		
Turn-Off Time	$t_{d(off)}$ t_f			40		
				12		

TYPICAL CHARACTERISTICS

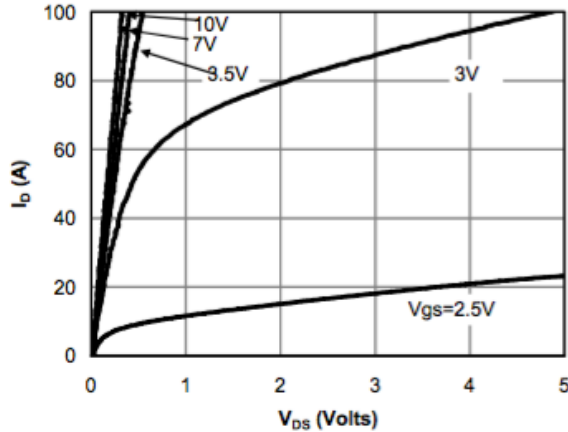


Fig 1: On-Region Characteristics (Note E)

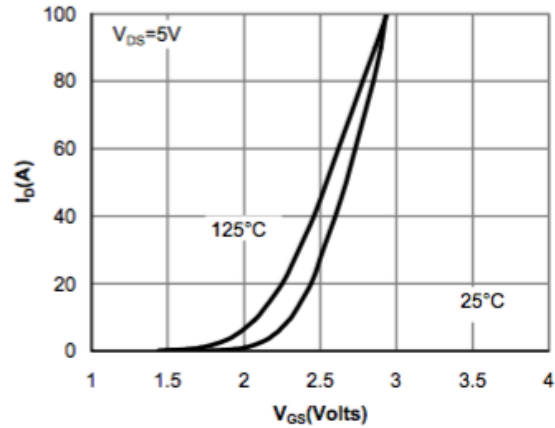


Figure 2: Transfer Characteristics (Note E)

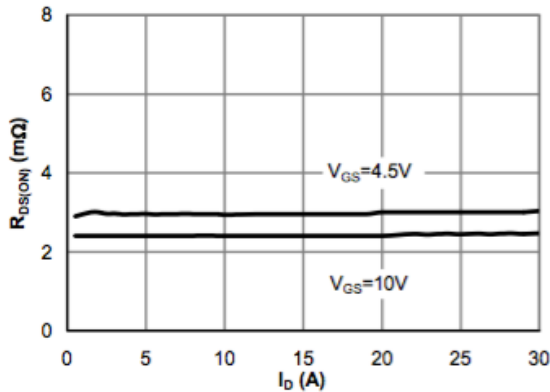


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

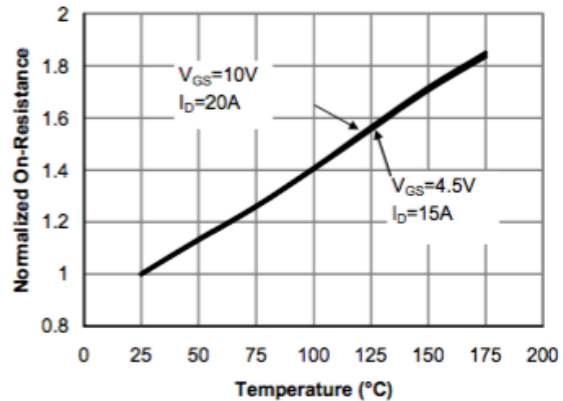


Figure 4: On-Resistance vs. Junction Temperature (Note E)

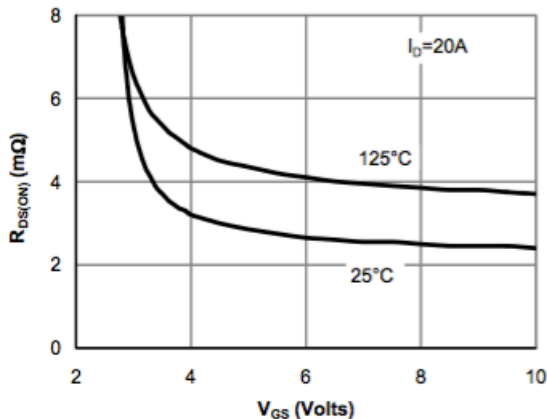


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

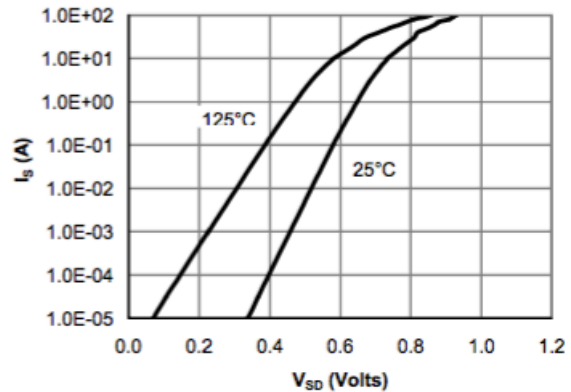


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL CHARACTERISTICS

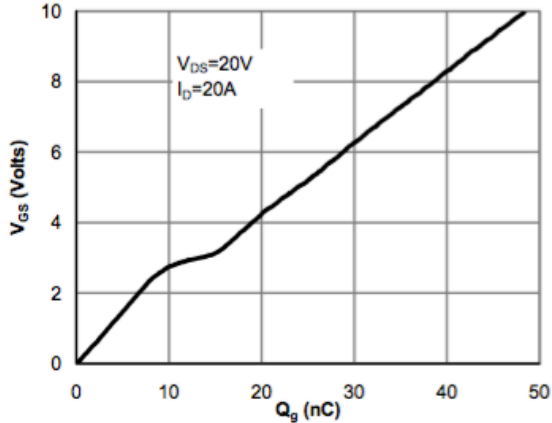


Figure 7: Gate-Charge Characteristics

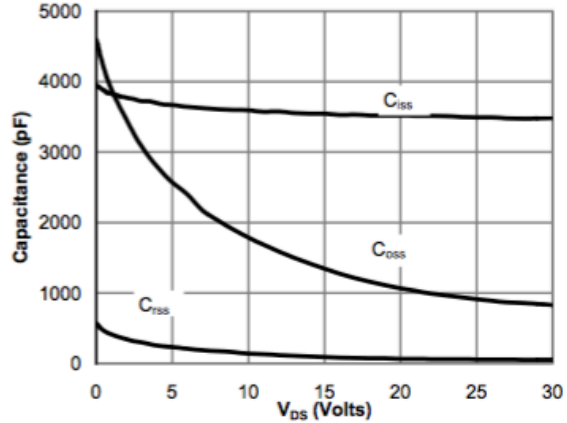


Figure 8: Capacitance Characteristics

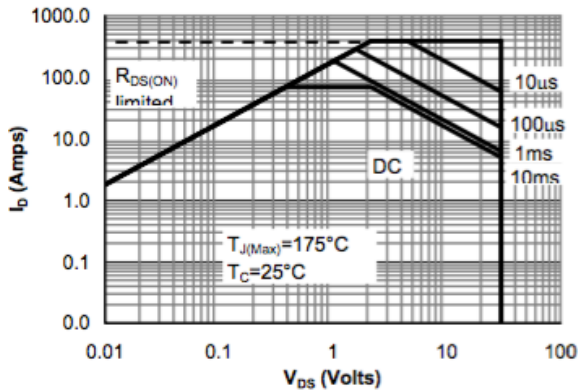


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

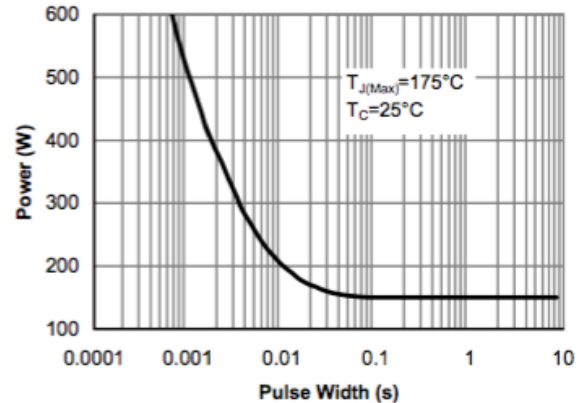


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

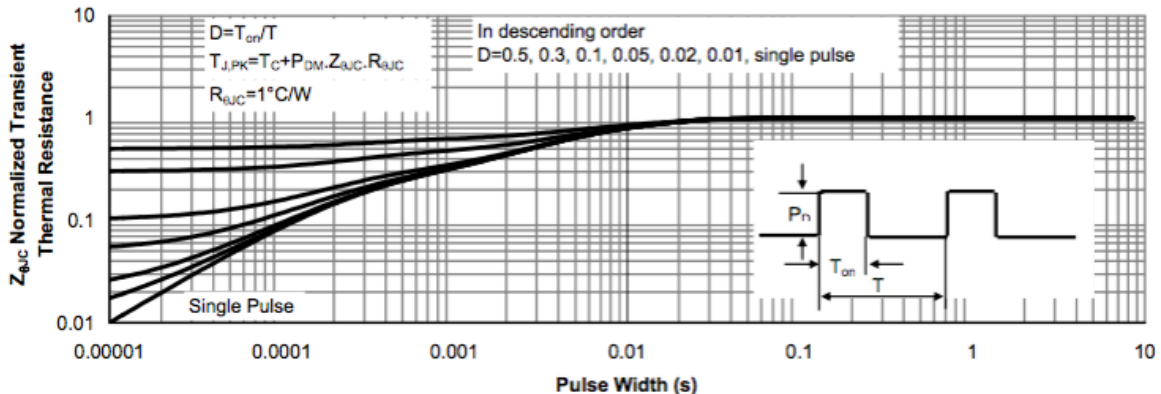


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL CHARACTERISTICS

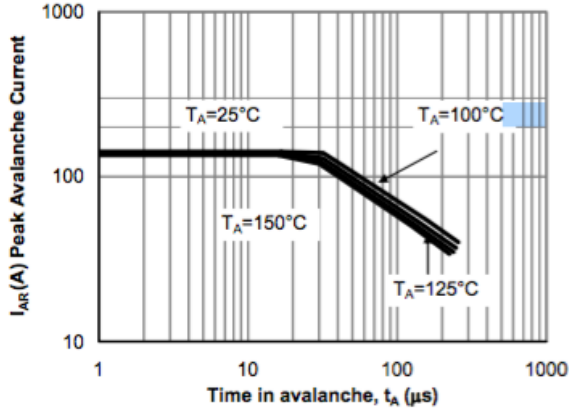


Figure 12: Single Pulse Avalanche capability (Note C)

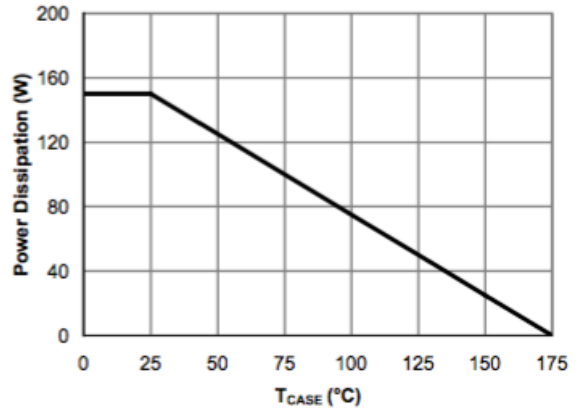


Figure 13: Power De-rating (Note F)

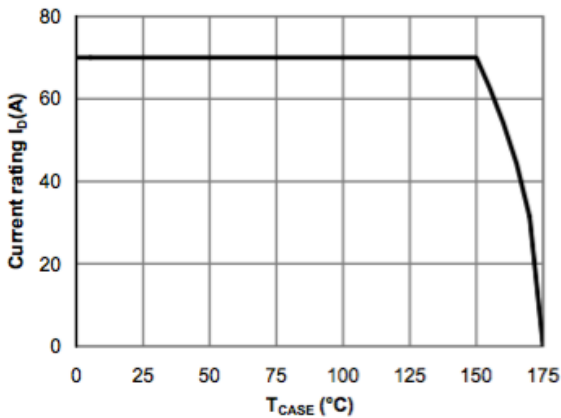


Figure 14: Current De-rating (Note F)

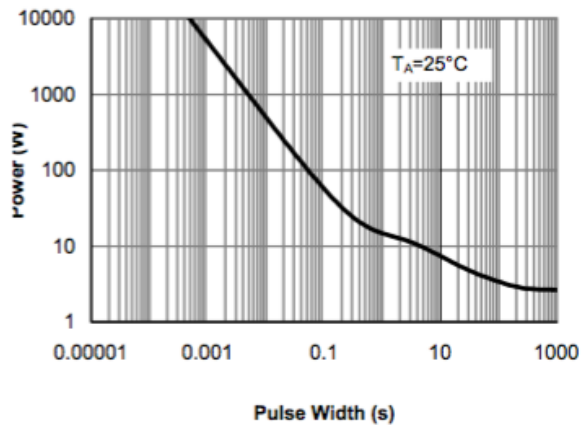


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)

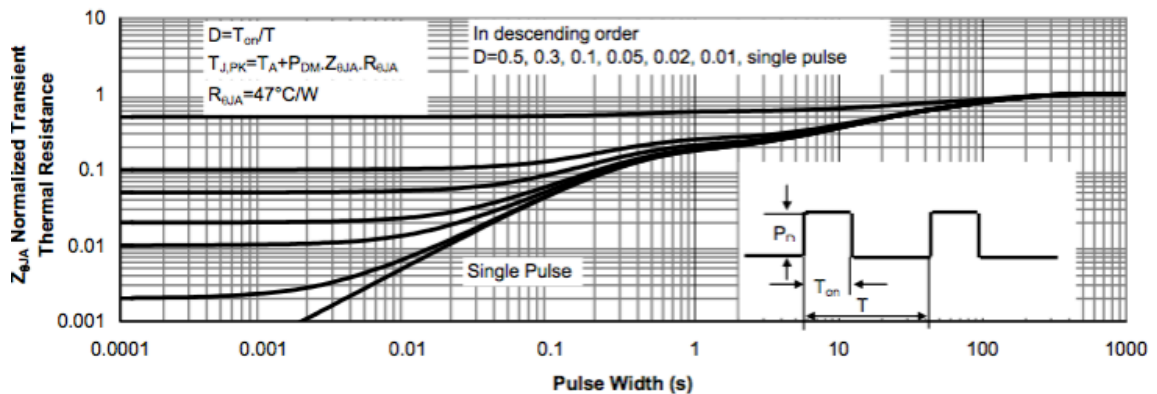
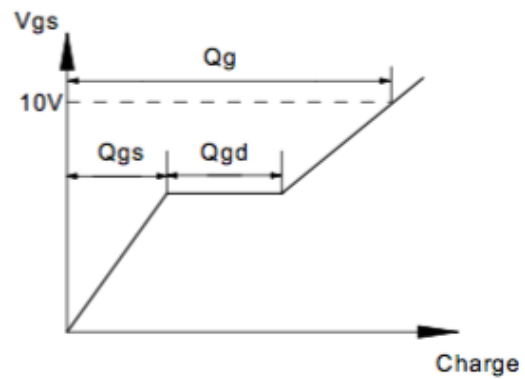
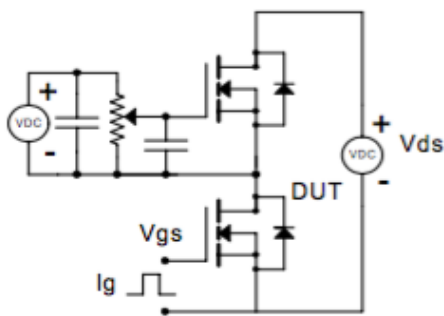
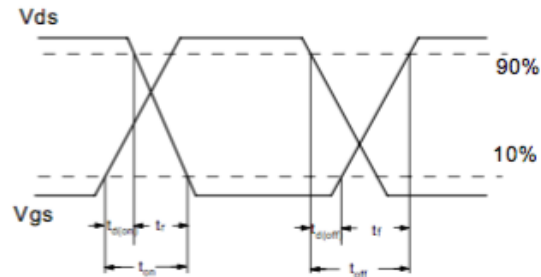
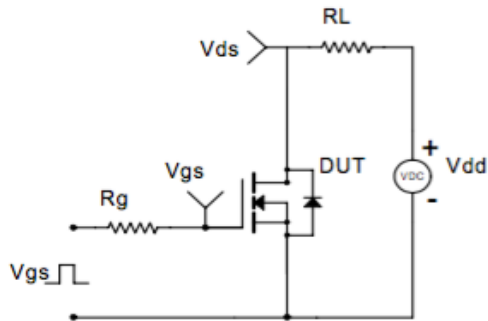


Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)

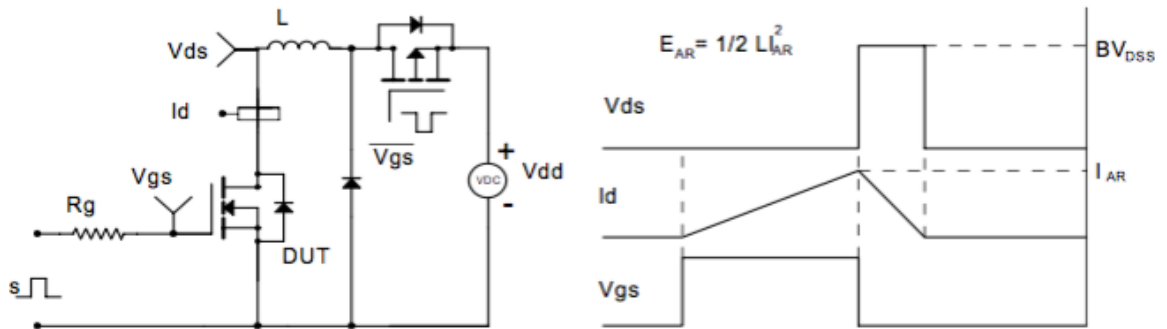
Gate Charge Test Circuit & Waveform



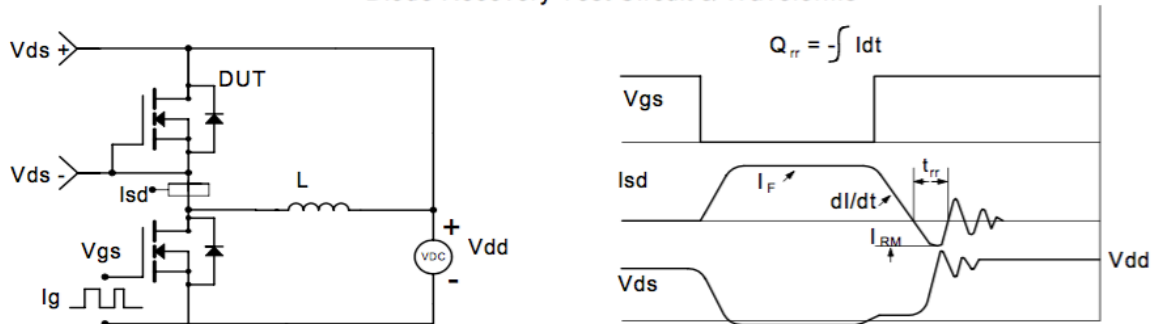
Resistive Switching Test Circuit & Waveforms



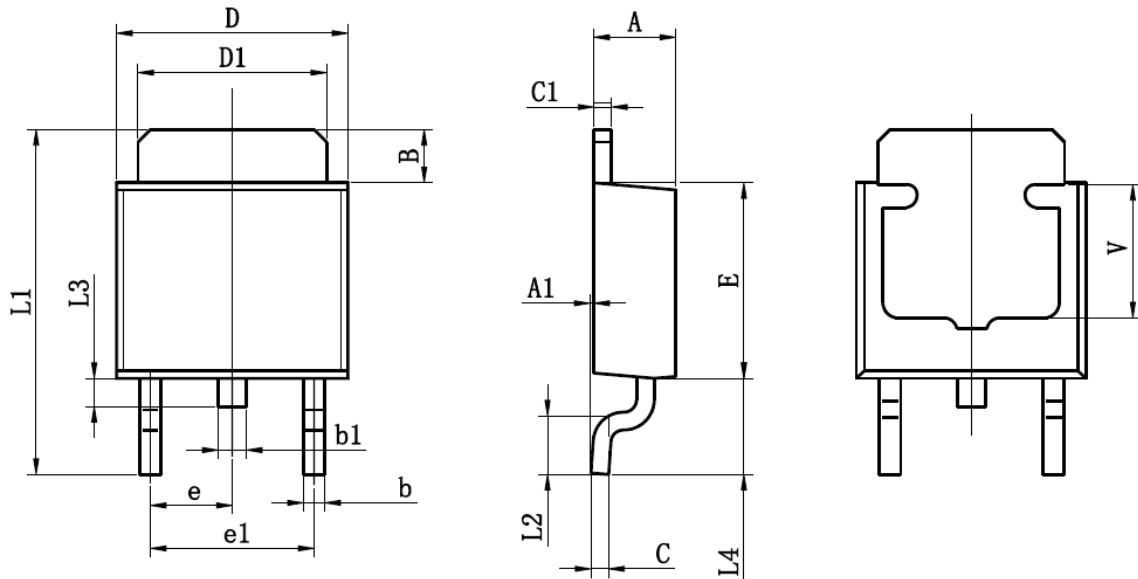
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



TO-252-2L PACKAGE OUTLINE :



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
B	1.350	1.650	0.053	0.065
b	0.500	0.700	0.020	0.028
b1	0.700	0.900	0.028	0.035
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	5.700	0.213	0.224
e	2.300TYP		0.091TYP	
e1	4.500	4.700	0.177	0.185
L1	9.500	9.900	0.374	0.390
L2	1.400	1.780	0.055	0.070
L3	0.650	0.950	0.026	0.037
L4	2.550	2.900	0.100	0.114
V	3.80REF		0.150REF	